

General Description

The MAX2651/MAX2652/MAX2653 silicon germanium (SiGe), low-noise amplifiers (LNAs) are intended for use in GSM900, DCS1800, and PCS1900 band wireless handsets. The MAX2651/MAX2652 consist of two LNAs, one optimized for the GSM900 band and the other optimized for the DCS1800/PCS1900 bands. They feature a band-select pin to switch between the two LNAs, as well as a gain-step input to reduce the gain of each LNA by 20dB and reduce supply current. The MAX2652 is functionally equivalent to the MAX2651, but features a lowpower shutdown mode. The MAX2653 consists of a single LNA optimized for the DCS1800 and PCS1900 bands, and has a shutdown feature and a 20dB gain step.

The MAX2652 and MAX2653 together form an ideal solution for triple-band phone applications (GSM, DCS, and PCS bands).

The MAX2651/MAX2652/MAX2653 are fabricated using an advanced high-frequency SiGe bipolar process. As a result, all devices provide low noise figure, high gain, and high input third-order intercept point (IP3) performance at the GSM, DCS, and PCS bands. A pull-up resistor to VCC at each LNA output allows for gain adjustability. A minimal number of external components are needed for input and output matching, helping to reduce board space.

The MAX2651/MAX2652 are packaged in a 10-pin µMAX, while the MAX2653 is packaged in an 8-pin µMAX. All devices operate from a single +2.7V to +3.3V supply.

Applications

GSM900/DCS1800 Dual-Band Phones GSM900/DCS1800/PCS1900 Triple-Band Phones DCS1800 or PCS1900 Single-Mode Phones IS-136 TDMA Dual-Band Phones

Features

- ♦ Wide Operating Frequency Range 800MHz to 1000MHz (MAX2651/52) 1800MHz to 2000MHz (MAX2651/52/53)
- **♦ Excellent Low-Noise Performance** 1.2dB/1.3dB over GSM Receive Band (MAX2651/52) 1.8dB/1.8dB/1.7dB over DCS Receive Band (MAX2651/52/53)
- ♦ High Gain

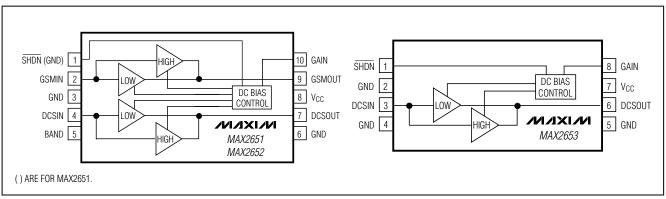
18dB over GSM Receive Band (MAX2651/52) 18dB/17.5dB/18.5dB over DCS Receive Band (MAX2651/52/53)

- ♦ 20dB Gain Reduction in Low-Gain Mode
- ♦ Externally Adjustable Gain
- ♦ +2.7V to +3.3V Single-Supply Operation
- **♦ Low Supply Current** 5.4mA to 7.0mA in High-Gain Mode 2.2mA in Low-Gain Mode
- ♦ 0.25µA Shutdown Current (MAX2652/53)

Ordering Information

PART	TEMP RANGE	PIN-PACKAGE
MAX2651EUB	-40°C to +85°C	10 μMAX
MAX2652EUB	-40°C to +85°C	10 μMAX
MAX2653EUA	-40°C to +85°C	8 µMAX

Pin Configurations/Functional Diagrams



MIXIM

Maxim Integrated Products 1

For pricing, delivery, and ordering information, please contact Maxim/Dallas Direct! at 1-888-629-4642, or visit Maxim's website at www.maxim-ic.com.

ABSOLUTE MAXIMUM RATINGS

V _{CC} to GND	0.3V to +6V	10-Pin μMAX (derate 5.6mW/°C above	+70°C)444mW
SHDN, GAIN, BAND to GND0.3V to (V	(CC + 0.3V)	Operating Temperature Range	40°C to +85°C
GSMIN, DCSIN1.0V peak	(+10dBm)	Junction Temperature	
Input Current (all digital inputs)	±10mA	Storage Temperature Range	65°C to +150°C
Continuous Power Dissipation		Lead Temperature (soldering, 10s)	+300°C
8-Pin uMAX (derate 4.5mW/°C above +70°C)	362mW		

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



CAUTION! ESD SENSITIVE DEVICE

DC ELECTRICAL CHARACTERISTICS—MAX2651

 $(V_{CC} = +2.7V \text{ to } +3.3V, \text{ BAND} = \text{GAIN} = V_{CC}, \text{ no input signal, all input/output ports terminated in } 50\Omega, T_A = -40^{\circ}\text{C} \text{ to } +85^{\circ}\text{C}, \text{ unless } 10^{\circ}\text{C} \text{ to } 10^{\circ}\text$ otherwise noted. Typical values are at $V_{CC} = +3V$, $T_A = +25$ °C.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Voltage Range	Vcc		2.7		3.3	V
Input Supply Current		DCS band, high-gain mode (BAND = GAIN = V _{CC})		5.7	8.7	
	loo	DCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)		2.2	3.3	mA
	Icc	GSM band, high-gain mode (BAND = GND, GAIN = V _{CC})		5.9	9.6	IIIA
		GSM band, low-gain mode (BAND = GND, GAIN = V _{CC})		2.2	3.6	
Input Logic Threshold High	V _{IH}				1.5	V
Input Logic Threshold Low	VIL		0.5			V
Input Logic High Current	lін	VIN = VCC		1.5	μΑ	
Input Logic Low Current	I _I L	V _{IN} = GND	-1.5			μΑ

DC ELECTRICAL CHARACTERISTICS—MAX2652

(V_{CC} = +2.7V to +3.3V, BAND = GAIN = V_{CC}, no input signal, all input/output ports terminated in 50Ω, T_A = -40°C to +85°C, unless otherwise noted. Typical values are at $V_{CC} = +3V$, $T_A = +25$ °C.) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Voltage Range	V _{CC}		2.7		3.3	V
January Community		DCS band, high-gain mode (BAND = GAIN = V _{CC})		7.0	11.0	
	loo	DCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)		2.3	3.6	mA
Input Supply Current	Icc	GSM band, high-gain mode (BAND = GND, GAIN = V _{CC})		7.2	11.0	IIIA
		GSM band, low-gain mode (BAND = GND, GAIN = VCC)		2.4	3.7	
Shutdown Supply Current		SHDN = GND	SHDN = GND			

DC ELECTRICAL CHARACTERISTICS—MAX2653

 $(V_{CC} = +2.7V \text{ to } +3.3V, \overline{SHDN} = GAIN = V_{CC}, \text{ no input signal, all input/output ports terminated in } 50\Omega, T_A = -40^{\circ}C \text{ to } +85^{\circ}C, \text{ unless otherwise noted.}$ Typical values are at $V_{CC} = +3V, T_A = +25^{\circ}C.$) (Note 1)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Logic Threshold High	VIH				1.5	V
Input Logic Threshold Low	VIL		0.5			V
Input Logic High Current	lін	VIN = VCC			1.5	μΑ
Input Logic Low Current	I _I L	V _{IN} = GND	-1.5			μA
Input Voltage Range	Vcc		2.7		3.3	V
Input Supply Current	loo	DCS band, high-gain mode (GAIN = V _{CC})		5.4	8.5	mA
Input Supply Current	Icc	DCS band, low-gain mode (GAIN = GND)		2.2	3.2	IIIA
Shutdown Supply Current	ISHDN	SHDN = GND		0.25		μΑ
Input Logic Threshold High	VIH				1.5	V
Input Logic Threshold Low	VIL		0.5			V
Input Logic High Current	lін	VIN = VCC			3	μA
Input Logic Low Current	IIL	V _{IN} = GND	-1.5			μA

Note 1: Devices are production tested at $T_A = +25$ °C. Minimum and maximum limits are guaranteed by design and characterization.

AC ELECTRICAL CHARACTERISTICS—MAX2651

(MAX2651 EV kit, f_{IN} = 945MHz (GSM band), f_{IN} = 1850MHz (DCS band), P_{IN} = -30dBm, input and output matching networks are optimized for the frequency band of interest, all input/output ports terminated in 50 Ω , V_{CC} = +3V, V_{CC} = +25VC, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	COND	MIN	TYP	MAX	UNITS	
Input Frequency Range	fiN	DCS band (BAND = V _{CC})		1805		1880	MHz
(Note 3)	III	GSM band (BAND = GND))	925		960	IVIIIZ
		DCS band, high-gain mode (BAND = GAIN =	TA = +25°C	16.5	18	19.5	
		V _{CC})	$TA = -40^{\circ}C \text{ to } +85^{\circ}C$	16		20	
		DCS band, low-gain mode (BAND = V _{CC} ,	TA = +25°C	-3.5	-2	-0.5	
Power Gain (Note 4)	G	GAIN = GND)	$TA = -40^{\circ}C \text{ to } +85^{\circ}C$	-4		0	dB
Tower dain (Note 4)	GSM band, high- mode (BAND = G GAIN = V _{CC}) GSM band, low-g	GSM band, high-gain	TA = +25°C	16.5	18	19.5	ab
		•	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	16		20	
		mode (BAND = GAIN =	TA = +25°C	-3.5	-2	-0.5	
			$TA = -40^{\circ}C \text{ to } +85^{\circ}C$	-4		0	
		DCS band, high-gain mod (BAND = GAIN = V _{CC})	de		1.8	2.05	
Noise Figure (Note 4)	NF	DCS band, low-gain mode (BAND = V _{CC} , GAIN = GN			5.5	6.0	dB
	GSM band, high-gain mo (BAND = GND, GAIN = '				1.2	1.4	GD
		GSM band, low-gain mod (BAND = GAIN = GND)	е		5.3	6.7	



AC ELECTRICAL CHARACTERISTICS—MAX2651 (continued)

(MAX2651 EV kit, f_{IN} = 945MHz (GSM band), f_{IN} = 1850MHz (DCS band), P_{IN} = -30dBm, input and output matching networks are optimized for the frequency band of interest, all input/output ports terminated in 50 Ω , V_{CC} = +3V, V_{CC} = +25VC, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS		MIN	TYP	MAX	UNITS							
		(Note 5)	DCS band, high-gain mode (BAND = GAIN = V _{CC})	-11.5	-10									
Input Third-Order Intercept Point	IIP3	(Note 5)	DCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)	-1.5	0.5		dBm							
input mira-order intercept i oint	111 5	(Note 6)	GSM band, high-gain mode (BAND = GND, GAIN = V _{CC})	-10.5	-8.5		, abiii							
		(Note o)	GSM band, low-gain mode (BAND = GND, GAIN = GND)	-2.5	0.5									
			d, high-gain mode GAIN = V _{CC})	-20	-18									
Input 1dB Compression Point	IP _{-1dB}		d, low-gain mode V _{CC} , GAIN = GND)	-9.5	-8		dBm							
input rab compression roint	11 - 10B		d, high-gain mode GND, GAIN = V _{CC})	-20	-18		ubiii							
			d, low-gain mode GND, GAIN = GND)	-10.5	-8.5									
	S ₁₁ ²		d, high-gain mode GAIN = V _{CC})		-11	-8.5								
			d, low-gain mode V _{CC} , GAIN = GND)		-14	-12								
Input Return Loss			d, high-gain mode GND, GAIN = V _{CC})		-11	-8.5	dB							
				nd, low-gain mode GAIN = GND)		-20	-15							
			d, high-gain mode GAIN = V _{CC})		-14	-10								
	10 12		d, low-gain mode V _{CC} , GAIN = GND)		-12	-10	15							
Output Return Loss	S ₂₂ ²		d, high-gain mode GND, GAIN = V _{CC})		-19	-15	dB							
			d, low-gain mode GAIN = GND)		-20	-15								
Reverse Isolation			d, high-gain mode GAIN = V _{CC})		-32	-29								
	S ₁₂ ² DCS (BAN GSM (BAN GSM	(RANIC		d, low-gain mode V _{CC} , GAIN = GND)		-20	-18	-ID						
		S ₁₂ ²	S ₁₂ ²	S ₁₂ ²	S ₁₂ ²	512 -	512 2	512 -	S ₁₂ ²		d, high-gain mode GND, GAIN = V _{CC})		-39	-35
			id, low-gain mode GAIN = GND)		-22	-20								
Reverse Isolation		(BAND = GSM bar (BAND = GSM bar	V _{CC} , GAIN = GND) d, high-gain mode GND, GAIN = V _{CC}) d, low-gain mode		-39	-35	dB							

AC ELECTRICAL CHARACTERISTICS—MAX2652

(MAX2652 EV kit, f_{IN} = 945MHz (GSM band), f_{IN} = 1850MHz (DCS band), P_{IN} = -30dBm, input and output matching networks are optimized for the frequency band of interest, all input/output ports terminated in 50Ω , V_{CC} = +3V, T_A = +25°C, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL		COND	ITIONS	MIN	TYP	MAX	UNITS				
Input Frequency Range	for	DCS ban	d (BAND = V _{CC})		1805		1880	MHz				
(Note 3)	fIN	GSM bar	nd (BAND = GND))	925		960	IVIDZ				
			d, high-gain AND = GAIN =	TA = +25°C	16	17.5	19					
		V _{CC})	((VD = G/()(V =	$TA = -40^{\circ}C \text{ to } +85^{\circ}C$	15.5		19.5					
			d, low-gain AND = V _{CC} ,	TA = +25°C	-3.5	-2	-0.5					
Power Gain (Note 4)	G	GAIN = 0		$TA = -40^{\circ}C \text{ to } +85^{\circ}C$	-4		0	dB				
1 ower dain (Note 4)	G G		nd, high-gain AND = GND,	TA = +25°C	16.5	18	19.5	GB				
		GAIN = V		$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	16		20					
			nd, low-gain AND = GAIN =	TA = +25°C	-4.0	-2	-0.5					
		GND)	(IVD = G/(IIV =	$TA = -40^{\circ}C \text{ to } +85^{\circ}C$	-4.5		0					
			d, high-gain mod GAIN = V _{CC})	de		1.8	2.0					
Noise Figure (Note 4)	NF	DCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)			5.8	6.3	B dB					
Noise Figure (Note 4)	INI		nd, high-gain moo GND, GAIN = V			1.3	1.5	QD.				
			nd, low-gain mod GAIN = GND)	е		5.5	6.7					
		(1) (5)	DCS band, hig (BAND = GAIN		-8.5	-7						
Input Third-Order				libo.	IID0	(Note 5)	DCS band, low (BAND = V _{CC} ,		0	1.5		dBm
Intercept Point	IIP3	(1)	GSM band, hig (BAND = GND		-9	-7.5		abiii				
		(Note 6)	GSM band, low (BAND = GND	v-gain mode , GAIN = GND)	0.5	2.5						
Input 1dB Compression Point			d, high-gain mod GAIN = V _{CC})	de	-18	-16.5						
	IP _{-1dB}		DCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)		-10.5	-8		dBm				
	IF-1dB		nd, high-gain mod GND, GAIN = V		-18	-16.5		ubiii				
			nd, low-gain mod GND, GAIN = G		-10	-8.5						



AC ELECTRICAL CHARACTERISTICS—MAX2652 (continued)

(MAX2652 EV kit, f_{IN} = 945MHz (GSM band), f_{IN} = 1850MHz (DCS band), P_{IN} = -30dBm, input and output matching networks are optimized for the frequency band of interest, all input/output ports terminated in 50 Ω , V_{CC} = +3 V_{CC} = +25 V_{CC} , unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNIT
		DCS band, high-gain mode (BAND = GAIN = V _{CC})		-12	-9.5	
Input Return Loss	S ₁₁ ²	DCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)		-12	-9.5	dB
input neturi Loss		GSM band, high-gain mode (BAND = GND, GAIN = V _{CC})		-11	-9.5	uБ
		GSM band, low-gain mode (BAND = GAIN = GND)		-20	-15	
		DCS band, high-gain mode (BAND = GAIN = V _{CC})		-11	-9.5	
Output Return Loss	S ₂₂ ²	DCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)		-17	-13	dB
Output Hetum Loss		922	GSM band, high-gain mode (BAND = GND, GAIN = V _{CC})		-12.5	-11
		GSM band, low-gain mode (BAND = GAIN = GND)		-15	-13	
		DCS band, high-gain mode (BAND = GAIN = V _{CC})		-29	-26	
Reverse Isolation	S ₁₂ ²	DCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)		-19	-17	dB
		GSM band, high-gain mode (BAND = GND, GAIN = V _{CC})		-37	-34	ub
		GSM band, low-gain mode (BAND = GAIN = GND)		-23	-20	

AC ELECTRICAL CHARACTERISTICS—MAX2653

(MAX2653 EV kit, f_{IN} = 1850MHz (DCS band), f_{IN} = 1960MHz (PCS band), P_{IN} = -30dBm, input and output matching networks are optimized for the frequency band of interest, all input/output ports terminated in 50 Ω , V_{CC} = +3V, T_{A} = +25°C, unless otherwise noted.) (Note 2)

PARAMETER	SYMBOL	COND	ITIONS	MIN	TYP	MAX	UNITS	
Input Frequency Range	fIN	BAND = V _{CC}	DCS band	1805		1880	MHz	
(Note 3)	IIN	DAND = VCC	PCS band	1930		1990	IVII IZ	
		DCS and PCS band, high-gain mode	T _A = +25°C	17	18.5	20		
Power Gain (Note 4)	G	(BAND = GAIN = V _{CC})	$T_A = -40^{\circ}C \text{ to } +85^{\circ}C$	16		20	dB	
1 ower dain (Note 4)	a a	DCS and PCS band, low-gain mode (BAND =	T _A = +25°C	-4	-2.5	-1	ab	
		V _{CC} , GAIN = GND)	T _A = -40°C to +85°C	-4		0		
		High-gain mode	DCS band		1.7	1.9		
Noise Figure (Note 4)	NF	$(BAND = GAIN = V_{CC})$	PCS band		1.8	2.05	dB	
Thorse Figure (Note 4)		DCS and PCS band, low- (BAND = V _{CC} , GAIN = GN			5.3	6.7	ub	
Input Third-Order Intercept Point	IIP3		DCS and PCS band, high-gain mode (BAND = V _{CC} , GAIN = GND)		-8.5		dBm	
(Notes 5, 7)	IIF3	DCS and PCS band, low- (BAND = V _{CC} , GAIN = GI	-1	+1.5		UDIII		
Input 1dB Compression	ID	DCS and PCS band, high (BAND = GAIN = V _{CC})	-gain mode	-20	-18		dП	
Point	IP _{-1dB}	DCS and PCS band, low- (BAND = V _{CC} , GAIN = GI		-9	-7		- dB	
	10 12	DCS and PCS band, high (BAND = GAIN = V _{CC})	-gain mode		-11	-8.5	10	
Input Return Loss	S ₁₁ ²	DCS and PCS band, low- (BAND = V _{CC} , GAIN = GI			-11	-9.5	- dB	
	10 12	DCS and PCS band, high (BAND = GAIN = V _{CC})		-12	-9.5	ID.		
Output Return Loss S ₂₂	S ₂₂ ²	DCS and PCS band, low-gain mode (BAND = V _{CC} , GAIN = GND)			-15	-12	- dB	
		High-gain mode (BAND	DCS band		-35	-31		
Reverse Isolation	S ₁₂ ²	= GAIN = V _{CC})	PCS band		-33	-29	-29 dB	
1 16 vel 56 1501ation	512	Low-gain mode (BAND =	DCS band		-21	-18	l ub	
		V _{CC} , GAIN = GND)	PCS band		-21	-18		

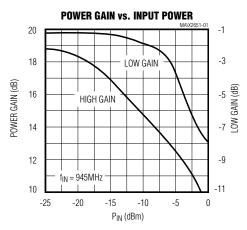
- Note 2: Minimum and maximum limits are guaranteed by design and characterization, but not production tested.
- **Note 3:** The part has been fully characterized at the specified frequency range. Operation outside of this range is possible but not guaranteed.
- Note 4: Specification excludes circuit board losses.
- **Note 5:** Measured with two tones, $f_{IN1} = 1850MHz$, $f_{IN2} = 1850.8MHz$, $P_{IN} = -33dBm$ for each tone.
- **Note 6:** Measured with two tones, $f_{IN1} = 945MHz$, $f_{IN2} = 945.8MHz$, $P_{IN} = -33dBm$ for each tone.
- Note 7: Measured with two tones, $f_{1N1} = 1960MHz$, $f_{1N2} = 1960.8MHz$, $P_{1N} = -33dBm$ for each tone.

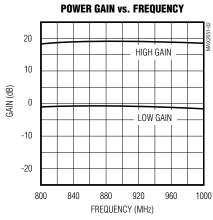


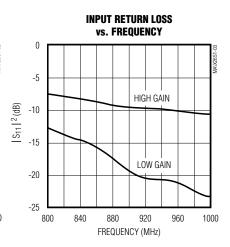
Typical Operating Characteristics

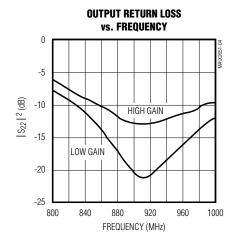
(MAX2651 EV kit, $V_{CC} = +3.0V$, input and output matched with recommended matching networks, $T_A = +25^{\circ}C$, unless otherwise noted.)

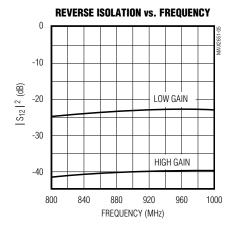
MAX2651 (GSM Band)

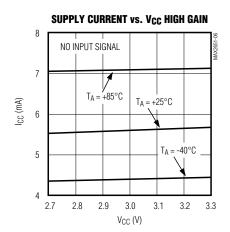


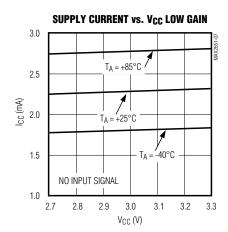










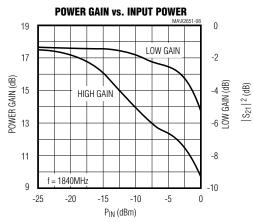


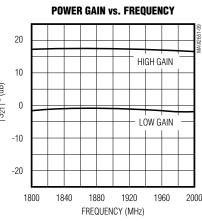
NIXIN

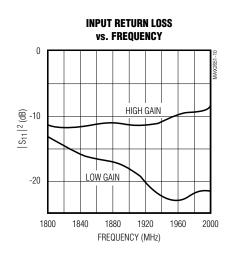
Typical Operating Characteristics (continued)

(MAX2651 EV kit, $V_{CC} = +3.0V$, input and output matched with recommended matching networks, $T_A = +25$ °C, unless otherwise noted.)

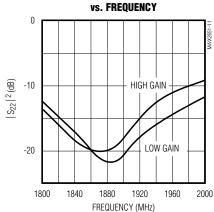
MAX2651 (DCS Band)

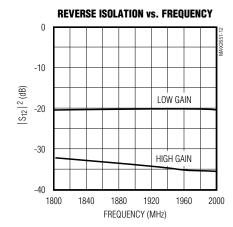




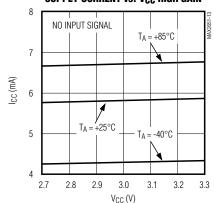


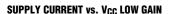
OUTPUT RETURN LOSS

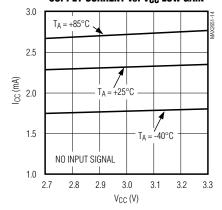




SUPPLY CURRENT vs. V_{CC} HIGH GAIN

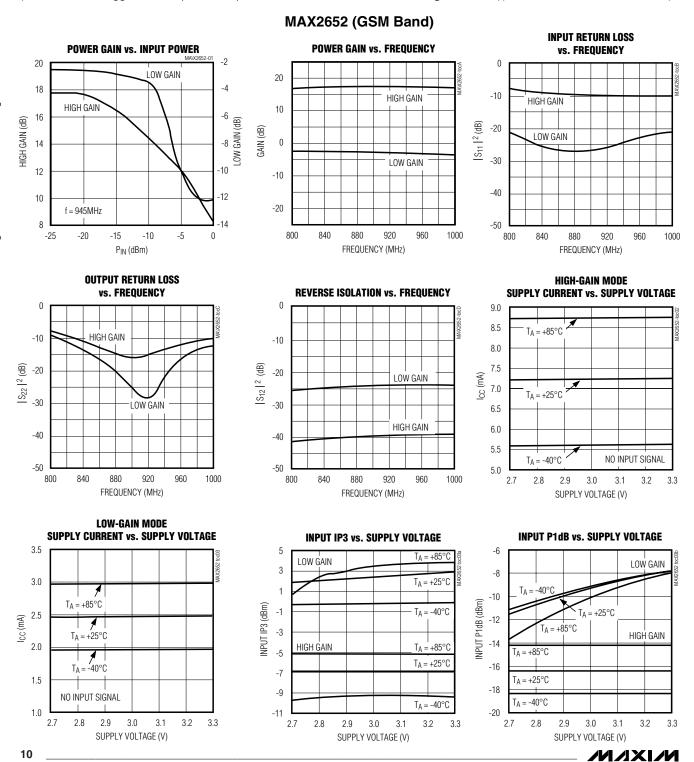






Typical Operating Characteristics (continued)

(MAX2652 EV kit, $V_{CC} = +3.0V$, input and output matched with recommended matching networks, $T_A = +25$ °C, unless otherwise noted.)



SUPPLY VOLTAGE (V)

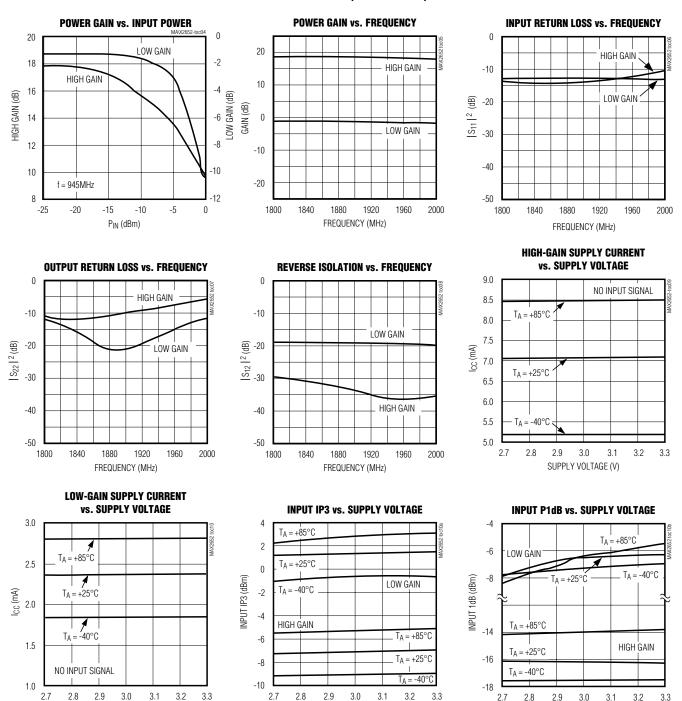
11

GSM900 and DCS1800/PCS1900 Dual-Band, Low-Noise Amplifiers

Typical Operating Characteristics (continued)

(MAX2652 EV kit, $V_{CC} = +3.0V$, input and output matched with recommended matching networks, $T_A = +25$ °C, unless otherwise noted.)

MAX2652 (DCS Band)



SUPPLY VOLTAGE (V)

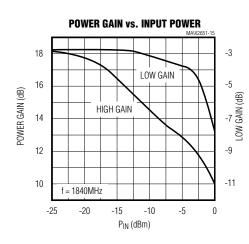
MIXIM

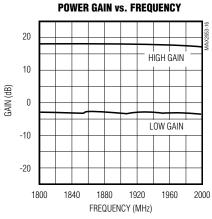
SUPPLY VOLTAGE (V)

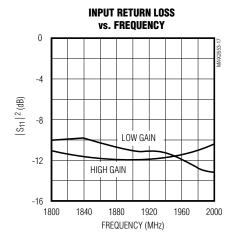
Typical Operating Characteristics (continued)

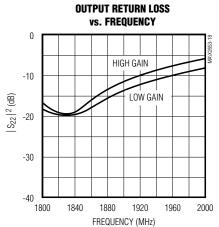
(MAX2653 EV kit, $V_{CC} = +3.0V$, input and output matched with recommended matching networks, $T_A = +25$ °C, unless otherwise noted.)

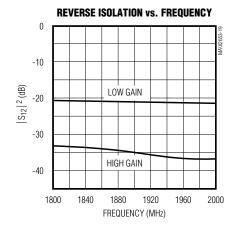
MAX2653 (DCS Band)

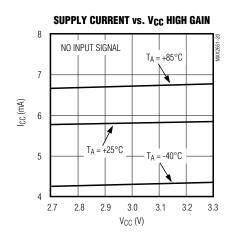


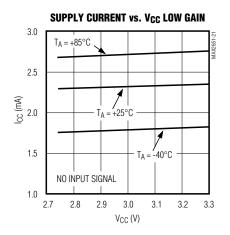












12 _______/N/JXI/M

Pin Description

	PIN		NAME	FUNCTION
MAX2651	MAX2652	MAX2653	INAME	FUNCTION
_	1	1	SHDN	Shutdown Logic Input. Drive low to enter shutdown; drive high or connect to V _{CC} for normal operation.
1, 3, 6	3, 6	2, 4, 5	GND	RF Ground. Connect to the ground plane as close to the IC as possible to minimize trace inductance.
2	2	_	GSMIN	RF Input for GSM Band
4	4	3	DCSIN	RF Input for DCS and PCS bands
5	5	_	BAND	Band-Select Logic Input. Drive BAND high to enable DCS/PCS LNA; drive low to enable GSM LNA.
7	7	6	DCSOUT	RF Output for DCS and PCS Bands
8	8	7	Vcc	Supply Voltage Input, +2.7V < V _{CC} < +3.3V
9	9	_	GSMOUT	RF Output for GSM Band
10	10	8	GAIN	Gain-Select Logic Input. Drive GAIN high for high-gain operation; drive GAIN low for low-gain operation.

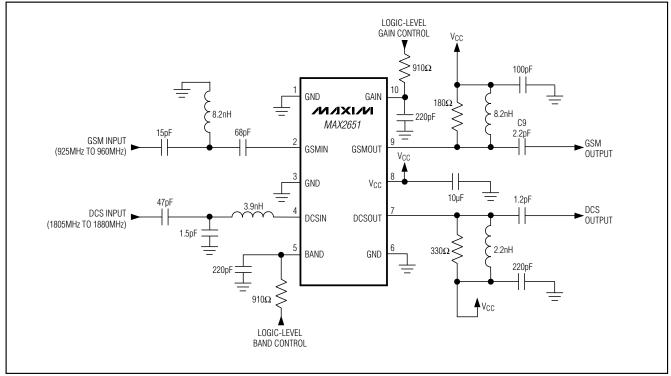


Figure 1. MAX2651 Typical Application Circuit



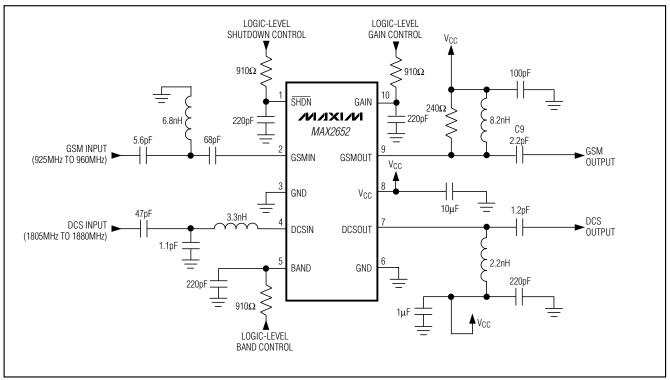


Figure 2. MAX2652 Typical Application Circuit

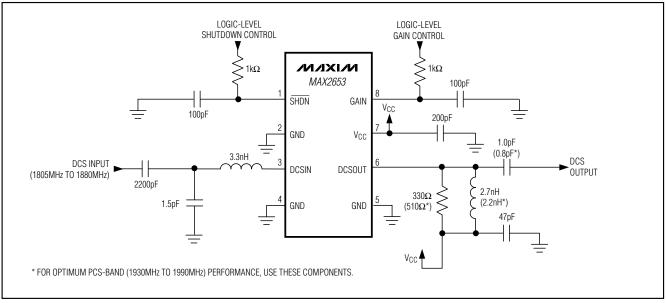


Figure 3. MAX2653 Typical Application Circuit

Detailed Description

Gain Select

The MAX2651/MAX2652/MAX2653 offer a step gain in the LNA to optimize the receiver's dynamic range. A logic-level low at GAIN reduces the active LNA's gain by about 20dB and reduces supply current by 3.5mA.

Shutdown Functionality

The MAX2652/MAX2653 offer a low-current shutdown feature. Drive SHDN low to power down the LNA and reduce supply current to less than 0.25µA.

Applications Information

External Components

The MAX2651/MAX2652/MAX2653 require matching circuits at their inputs and outputs for operation in a 50Ω system. The application circuits in Figures 1, 2, and 3 describe the matching circuits for each device's LNA; suggested component values, suppliers, and part numbers are listed in the MAX2651/MAX2652/MAX2653 EV kits manual. These values are optimized for best simultaneous noise figure, gain, and return loss performance.

Input and output impedance matching networks are very sensitive to layout-related parasitics. It is important to keep all matching components as close to the device as possible to minimize the effects of stray inductance and stray capacitance of PC board traces, particularly for the 1800MHz and 1900MHz bands.

Using the Collector Load Resistor to Set Gain

The MAX2651/MAX2652/MAX2653 provide open-collector output stages to allow an external resistor to set the gain. The collector pull-up resistors set the gain for each LNA to about 18dB. Lower gains are achieved by reducing this resistance, and higher gains are achieved by increasing it. The maximum achievable gain is defined by the maximum collector current swing. Note that the value of the collector gain-setting resistor principally defines the LNA's output impedance, and that the matching networks are tuned to match this impedance to 50Ω . Redefining the LNA gain by changing the collector gain-setting resistor requires retuning the output matching networks.

Layout and Power-Supply Bypassing

A properly designed PC board is essential to any RF/microwave circuit. Be sure to use controlled impedance lines on all high-frequency inputs and outputs. Proper grounding of the GND pins is fundamental; if the PC board uses a topside RF ground, connect all GND pins directly to it. For boards where the ground plane is not on the component side, it's best to connect all GND pins to the ground plane with plated throughholes close to the package.

To minimize coupling between different sections of the system, the ideal power-supply layout is a star configuration with a large decoupling capacitor at a central VCC node. The VCC traces branch out from this central node, each leading to a separate VCC node on the PC board. A second bypass capacitor that has low ESR at the RF frequency of operation is placed at the end of each trace. This arrangement provides local decoupling at the VCC pin. At high frequencies, any signal leaking out of one supply pin sees a relatively high impedance (formed by the VCC trace inductance) to the central VCC node and an even higher impedance to any other supply pin, as well as a low impedance to ground through its bypass capacitor.

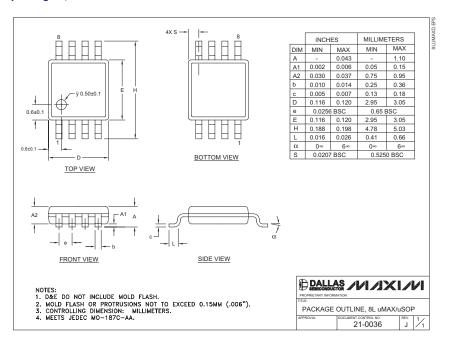
Chip Information

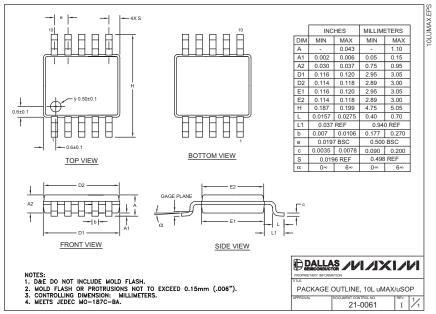
MAX2651 TRANSISTOR COUNT: 272 MAX2652 TRANSISTOR COUNT: 272 MAX2653 TRANSISTOR COUNT: 253



Package Information

(The package drawing(s) in this data sheet may not reflect the most current specifications. For the latest package outline information, go to www.maxim-ic.com/packages.)





Note: The packages for these devices do not feature the exposed pad.

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